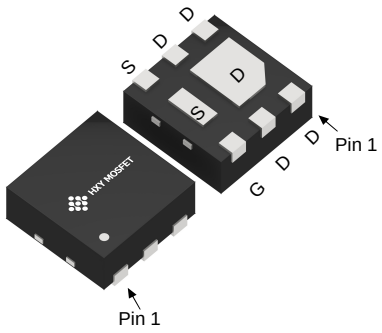
HXY1216BF

P-Channel Enhancement Mode MOSFET

Description

The HXY1216BF uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.



DFN2X2B-6L

General Features

V_{DS} = -15V,I_D = -16A

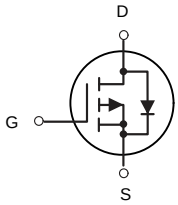
$R_{DS(ON)}$ < 18mΩ @ V_{GS}=-4.5V

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY1216BF	DFN2X2B-6L	1216 XXXX	5000

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-15	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current-Continuous	-16	A
I_{DM}	Drain Current-Pulsed	-65	A
P_D	Maximum Power Dissipation	2.8	W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient	50	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-15	-18	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C, I_D=-1mA	---	-0.022	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-15A	---	11	18	mΩ
		V_{GS}=-4.5V , I_D=-10A	---	14	22	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	---		V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25°C	---	---	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55°C	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±25V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-15A	---	19	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	13	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-15A	---	35	---	nC
Q_{gs}	Gate-Source Charge		---	5	---	
Q_{gd}	Gate-Drain Charge		---	10	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3Ω, I_D=-15A	---	11	---	ns
T_r	Rise Time		---	35	---	
$T_{d(off)}$	Turn-Off Delay Time		---	30	---	
T_f	Fall Time		---	10	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	2600	---	pF
C_{oss}	Output Capacitance		---	670	---	
C_{rss}	Reverse Transfer Capacitance		---	560	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-16	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25°C	---	---	-1.2	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AS}=-38A
4.The power dissipation is limited by 150˚C junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Electrical and Thermal Characteristics

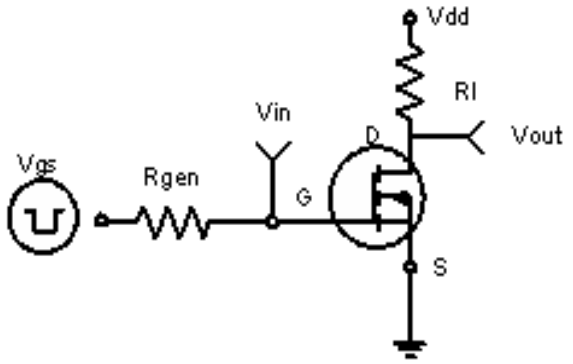


Figure 1:Switching Test Circuit

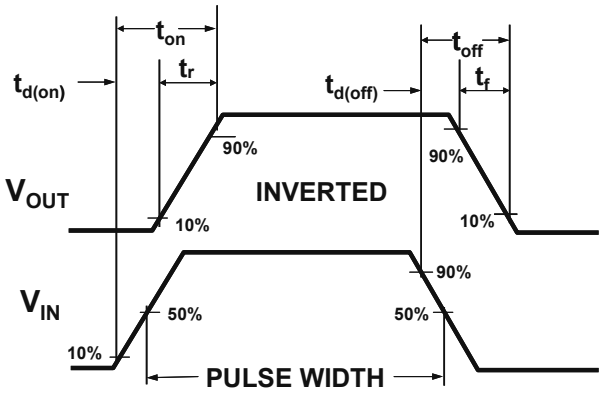
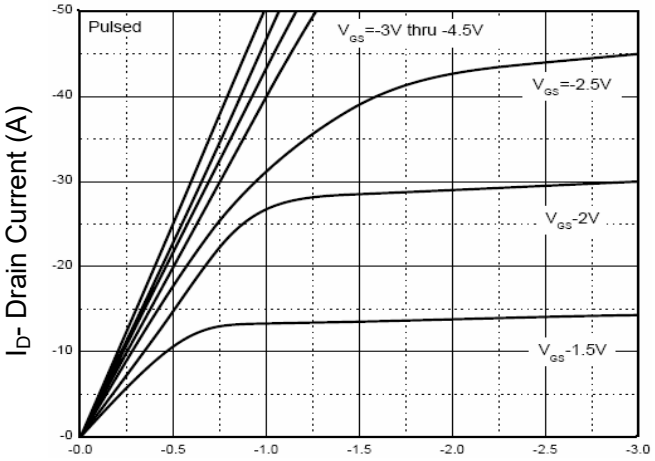
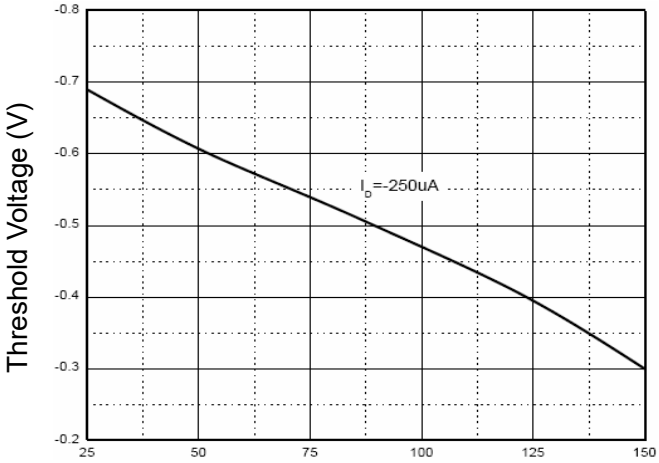


Figure 2:Switching Waveforms



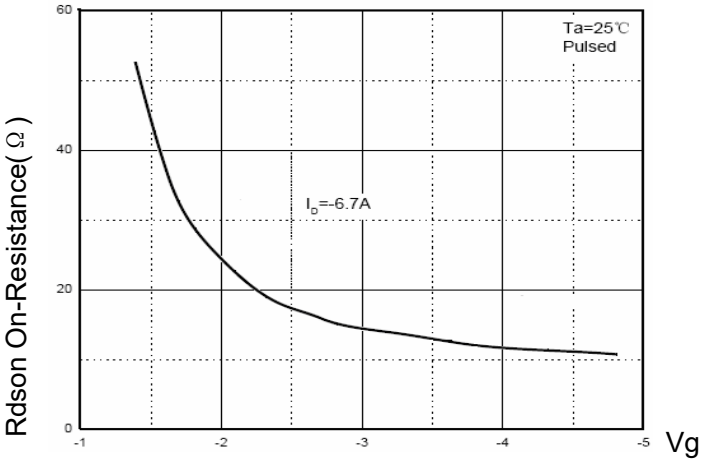
Vds Drain-Source Voltage (V)

Figure 3 Output Characteristics



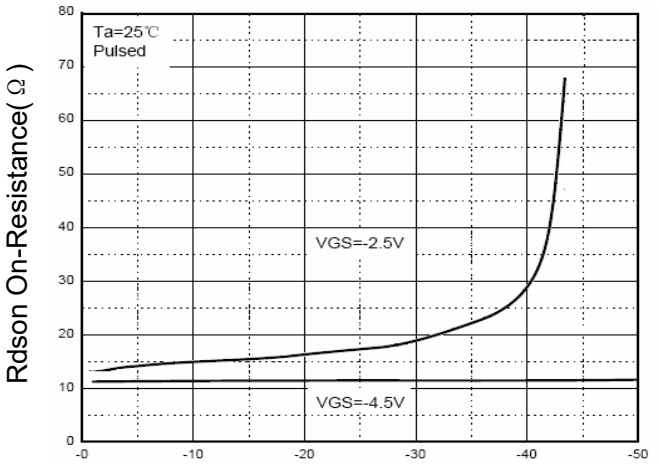
TJ-Junction Temperature(°C)

Figure 4 Drain Current



s Gate-Source Voltage (V)

Figure 5 Rdson vs Vgs



ID- Drain Current (A)

Figure 6 Drain-Source On-Resistance

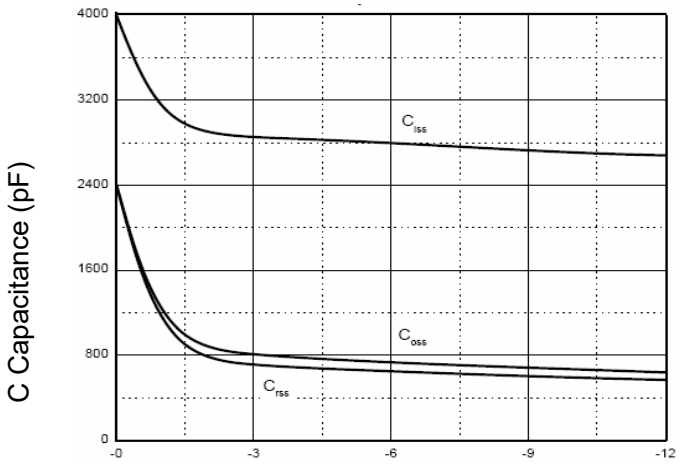


Figure 7 Capacitance vs Vds

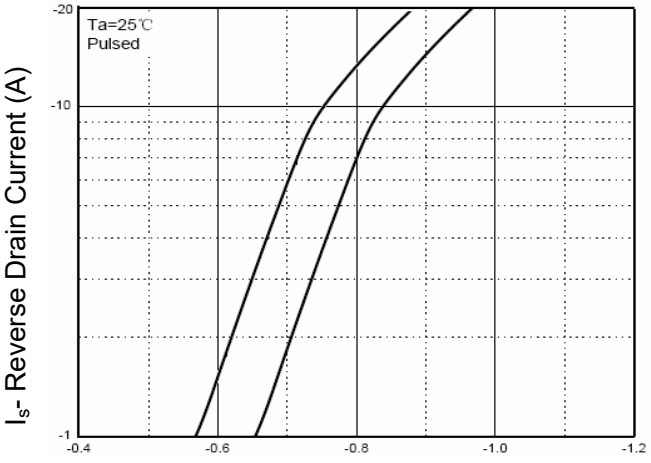
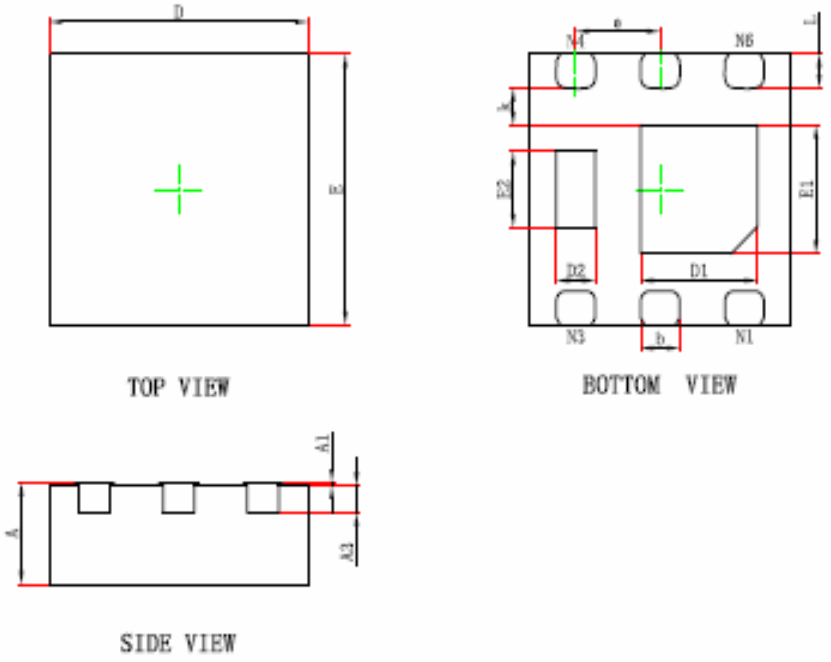


Figure 8 Source- Drain Diode Forward

DFN2X2B-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

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